20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D
20V	0.040Ω	5.4A

Description

This new generation of high density MOSFETs from Diodes Incorporated utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

Features

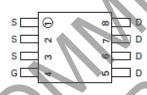
- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Profile SOIC Package

Applications

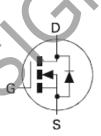
- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control



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Top View



Ordering Information

Part Number	Device Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXM64N02XTA	ZXM64N02	7	12mm Embossed	1000 Units
ZXM64N02XTC	ZXM64N02	13	12mm Embossed	4000 Units



NOT RECOMMENDED FOR NEW DESIGN - NO ALTERNATE PART

ZXM64N02X

Absolute Maximum Ratings

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	20	V
Gate- Source Voltage	V _{GS}	± 12	V
Continuous Drain Current ($V_{GS}=4.5V$; $T_A=25$ °C)(b) ($V_{GS}=4.5V$; $T_A=70$ °C)(b)	I _D	5.4 4.3	Α
Pulsed Drain Current (c)	I _{DM}	30	Α
Continuous Source Current (Body Diode)(b)	I _S	2.4	A
Pulsed Source Current (Body Diode)(c)	I _{SM}	30	A
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P_D	1.1 8.8	W mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	1.8 14.4	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	Ö.

Thermal Resistance

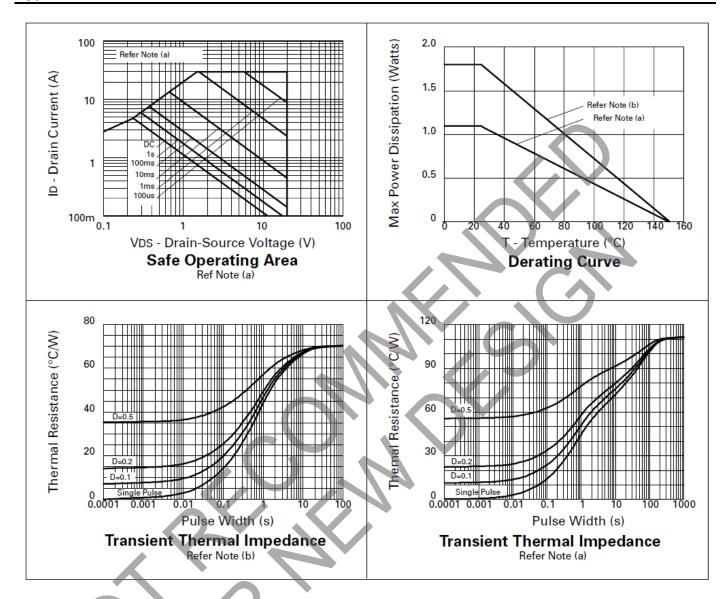
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	113	°C/W
Junction to Ambient (b)	$R_{\theta JA}$	70	°C/W

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- (b) For a device surface mounted on FR4 PCB measured at t≤10 secs.
- (c) Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.



Typical Characteristics



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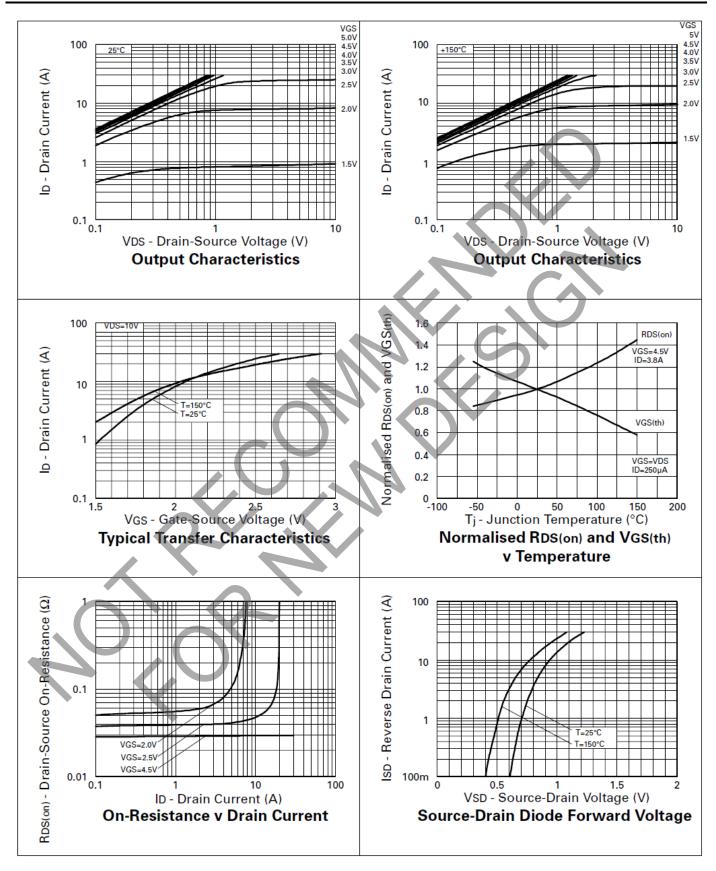
Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
STATIC							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	20			V	I _D =250μA, V _{GS} =0V	
Zero Gate Voltage Drain Current	I _{DSS}			1	μА	V _{DS} =20V, V _{GS} =0V	
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =± 12V, V _{DS} =0V	
Gate-Source Threshold Voltage	V _{GS(th)}	0.7			V	$I_D=250\mu A$, $V_{DS}=V_{GS}$	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.040 0.050	Ω	V _{GS} =4.5V, I _D =3.8A V _{GS} =2.7V, I _D =1.9A	
Forward Transconductance (3)	g _{fs}	6.1			S	V _{DS} =10V,I _D =1.9A	
DYNAMIC (3)		•	•				
Input Capacitance	C _{iss}		1100		pF	W AF W W OW	
Output Capacitance	Coss		350		pF	V _{DS} =15 V, V _{GS} =0V, f=1MHz	
Reverse Transfer Capacitance	C _{rss}		100		pF		
SWITCHING(2) (3)							
Turn-On Delay Time	t _{d(on)}		5.7		ns		
Rise Time	t _r		9.6	V	nŝ	$V_{DD} = 10V, I_{D} = 3.8A$	
Turn-Off Delay Time	t _{d(off)}		28.3		ns	$R_G=6.2\Omega$, $R_D=2.6\Omega$ (Refer to test	
Fall Time	t _f		11.6		ns	circuit)	
Total Gate Charge	Qg			16	nC	V -16V V -4 EV	
Gate-Source Charge	Ω_{gs}		1	3.5	nC	$V_{DS}=16V, V_{GS}=4.5V, I_{D}=3.8A$	
Gate Drain Charge	Q _{gd}			5.4	nC	(Řefer to test circuit)	
SOURCE-DRAIN DIODE							
Diode Forward Voltage (1)	V_{SD}			0.95	V	T _j =25°C, I _S =3.8A, V _{GS} =0V	
Reverse Recovery Time (3)	t _{rr}		23.7		ns	T _j =25°C, I _F =3.8A, di/dt= 100A/μs	
Reverse Recovery Charge(3)	Q _{rr}		13.3		nC	αι/αι= τουΑ/με	

⁽¹⁾ Measured under pulsed conditions. Width=300µs. Duty cycle ≤2%.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.

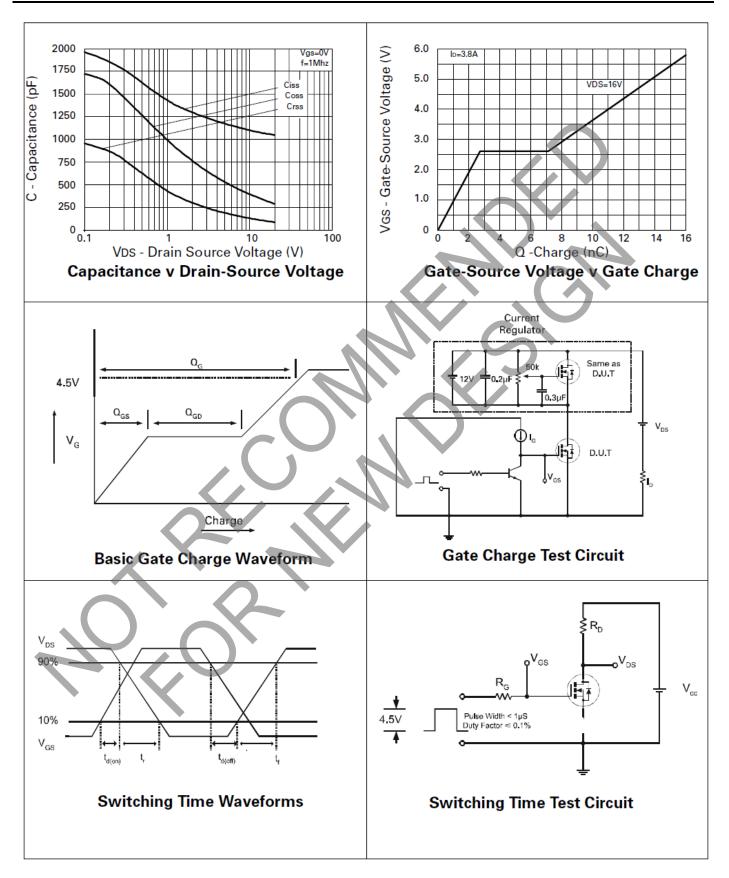


Typical Characteristics





Typical Characteristics (Cont.)

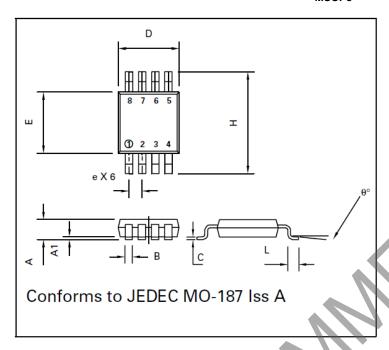




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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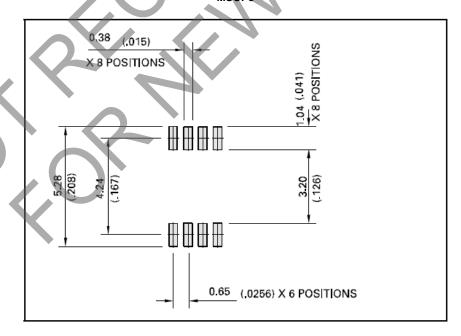


DIM	Millimetres		Inches	
	MIN	MAX	MIN	MAX
Α		1.10		0.043
A1	0.05	0.15	0.002	0.006
В	0.25	0.40	0.010	0.016
С	0.13	0.23	0.005	0.009
D	2.90	3.10	0.114	0.122
е	0.65	BSC	0.0256	BSC
E	2.90	3.10	0.114	0.122
Н	4.90	BSC	0.193	BSC
	0.40	0.70	0.016	0.028
q°	0°	6°	0°	6°

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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ZXM64N02X

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